

## AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

1. (Currently Amended) A mask comprising a pattern to modify a circuitry feature exposed in a radiation sensitive layer by transmitting modifying radiation according to the pattern to a region of the radiation sensitive layer containing the circuitry feature to reduce a distortion of the circuitry feature.
2. (Currently Amended) The mask of claim 1:

wherein the circuitry feature includes a corner rounded portion; and

wherein the pattern includes a radiation opaque portion corresponding to the circuitry feature having a corner cutout corresponding to the corner rounded portion to reduce the corner rounded portion by exposing the corner rounded portion with radiation transmitted through the corner cutout [[region]].
3. (Original) The mask of claim 1, wherein the pattern comprises a radiation intensity reducer to create the modifying radiation by reducing a portion of incident radiation provided to the mask and transmitting the modifying radiation to the region containing the circuitry feature.
4. (Currently Amended) The mask of claim [[1]]3, wherein the radiation intensity reducer comprises a plurality of proximate opaque subresolution features [[to reduce a portion of incident radiation that is provided to the subresolution features]].

5. (Currently Amended) The mask of claim [[1]]3, wherein the radiation intensity reducer comprises an applied phase shifting material [[that prevents]] to prevent a portion of radiation provided to the mask from exposing the radiation sensitive layer.
6. (Original) The mask of claim 1, wherein the pattern comprises a proximity effect distortion reducing feature selected from the group consisting of a serif to reduce corner rounding by emphasizing a corner of the circuitry feature and a hammerhead to reduce line shortening by emphasizing an end of the circuitry feature.
7. (Original) The mask of claim 1, wherein the pattern comprises a phase shifter.
8. (Original) The mask of claim 1:

wherein the circuitry feature includes a line segment having a pattern shift distortion that shifts the line segment to a first side of the line segment; and

wherein the pattern comprises a high radiation transmittance region corresponding to the first side of the line segment and a low radiation transmittance region corresponding to an opposite side of the line segment to reduce the pattern shift distortion by providing more of the modifying radiation to the high transmittance region than the low transmittance region.
9. (Currently Amended) The mask of claim 1, wherein the pattern [[further]] comprises:

an opaque portion to block a portion of radiation incident to the mask from exposing the circuitry feature; and

a transparent portion to transmit modifying radiation to the circuitry feature.
10. (Currently Amended) The mask of claim 1:

wherein the exposed circuitry feature comprises a linewidth; and

wherein the pattern [[is]] comprises a pattern to reduce the linewidth by transmitting linewidth reducing radiation to the region containing the linewidth.

11. (Currently Amended) The mask of claim 1, wherein the pattern [[is]] comprises a pattern to reduce a proximity effect distortion in the exposed circuitry feature by transmitting proximity effect reducing radiation to the region containing the circuitry feature.

Claims 12-17 (Cancelled)

18. (Currently Amended) A second mask [[having]] comprising a second pattern that corresponds to a first pattern of a first mask, the first pattern to expose an exposure feature in a radiation sensitive layer, the second pattern [[comprising]] having a transparent portion to reduce a proximity effect distortion of the exposure feature by providing modifying radiation to a region of the radiation sensitive layer that contains the exposure feature.
19. (Currently Amended) The [[second]] mask of claim 18:

wherein the exposure feature comprises a gate feature having a corner rounded region; and

wherein the transparent portion comprises a cutout portion [[sufficiently]] proximate to the corner rounded region to [[reduce the corner rounded region by providing]] provide radiation to the corner rounded region.
20. (Currently Amended) The [[second]] mask of claim 18, further comprising a pattern portion selected from the group consisting of: a phase shifter, a plurality of proximate subresolution features, and a layer of radiation reducing material to transmit substantially less radiation than a region of quartz of the mask.

Claims 21-24 (Cancelled)

25. (New) A set of masks comprising:
  - a first exposure mask having a first pattern; and
  - a second exposure mask having a second pattern, the second pattern including a subwavelength distortion reducing pattern corresponding to the first pattern.
26. (New) The set of masks of claim 25, further comprising an optical proximity correction pattern of the subwavelength distortion reducing pattern.
27. (New) The set of masks of claim 25, further comprising:
  - a corner portion of the first pattern; and
  - a corner cutout portion of the second pattern to reduce a corner rounding distortion corresponding to the corner portion by transmitting distortion reducing radiation to the corner rounding distortion.
28. (New) The set of masks of claim 25, wherein the subwavelength distortion reducing pattern further comprises a serif relative to the first pattern.
29. (New) The set of masks of claim 25, wherein the subwavelength distortion reducing pattern further comprises a hammerhead relative to the first pattern.
30. (New) The set of masks of claim 25, wherein the subwavelength distortion reducing pattern comprises an image balancing pattern including a pair of low and high transmittance regions that is reversed relative to a corresponding pair of low and high transmittance regions of the first pattern.